



FEATURES

- Circular active area
- Ideal for 193-400 nm detection
- 100% internal QE
- No cap for maximum responsivity
- Temporary cap taped on for shipping purposes

Dimensions are in inch [metric] units.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area	Ø 2.5 mm		5		mm ²
Responsivity, \mathcal{R}	@ 254 nm	0.09	0.115		A/W
Dark Current, I_{dr}	$V_R = 6 V$			1	nA
Reverse Breakdown Voltage, V_R	$I_R = 1 \mu A$	25	50		Volts
Capacitance, C	$V_R = 0 V$			2	nF
Rise Time	$V_R = 0 V$		1	2	μsec

THERMAL PARAMETERS

STORAGE AND OPERATING TEMPERATURE RANGE	
Storage Temperature Range	-20° TO 80°C
Maximum Junction Temperature	80°C
Lead Soldering Temperature ¹	240°C

¹0.0625" from case for 10 seconds.

Shipped with temporary cover to protect photodiode and wire bond.
Review Opto Diode "Handling Precautions for IRD Detectors" prior to removing cover.

